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(54) **Title:** EPI ISOLATION PLATE AND PARALLEL BLOCK PURGE FLOW TUNING FOR GROWTH RATE AND UNIFORMITY

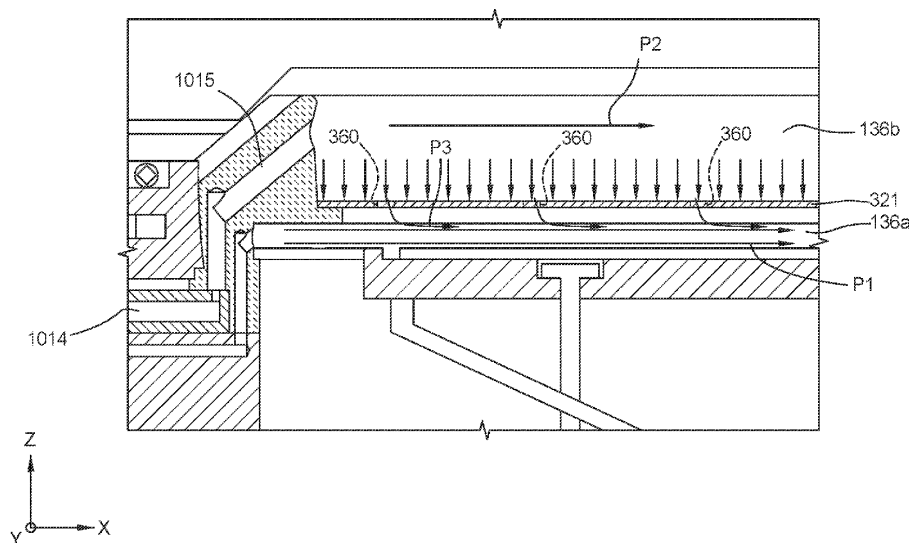


FIG. 4

(57) **Abstract:** A method and apparatus for processing substrates suitable for use in semiconductor manufacturing. The method includes heating a substrate positioned on a substrate support. The method includes flowing a purge gas over an isolation plate disposed above the substrate, the flowing the purge gas including diverting a portion of the purge gas below the isolation plate through a plurality of perforations in the isolation plate. The method includes flowing one or more process gases over the substrate to deposit a material on the substrate, the flowing of the one or more process gases over the substrate comprising guiding the one or more process gases through one or more flow paths defined at least in part by a space between the isolation plate and the substrate.

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